P-Channel Enhancement Mode Power MOSFET

Description

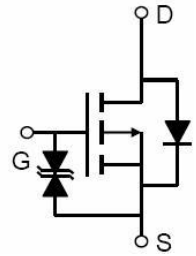
The G04P10HE uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} -100V
- I_D (at V_{GS} = -10V) -4A
- $R_{DS(ON)}$ (at V_{GS} = -10V) < 200mΩ
- $R_{DS(ON)}$ (at V_{GS} = -4.5V) < 250mΩ
- 100% Avalanche Tested
- RoHS Compliant
- ESD (HBM) : 6KV

Application

- Power switch
- DC/DC converters



Schematic diagram



SOT-223

Ordering Information

Device	Package	Marking	Packaging
G04P10HE	SOT-223	G04P10	2500pcs/Reel

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-100	V
Continuous Drain Current	T_C = 25ºC	I_D	-4	A
	T_C = 100ºC		-2.5	
Pulsed Drain Current (note1)		I_{DM}	-16	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		P_D	1.2	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 To 150	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient, t≤10s	R_{thJA}	100	ºC/W

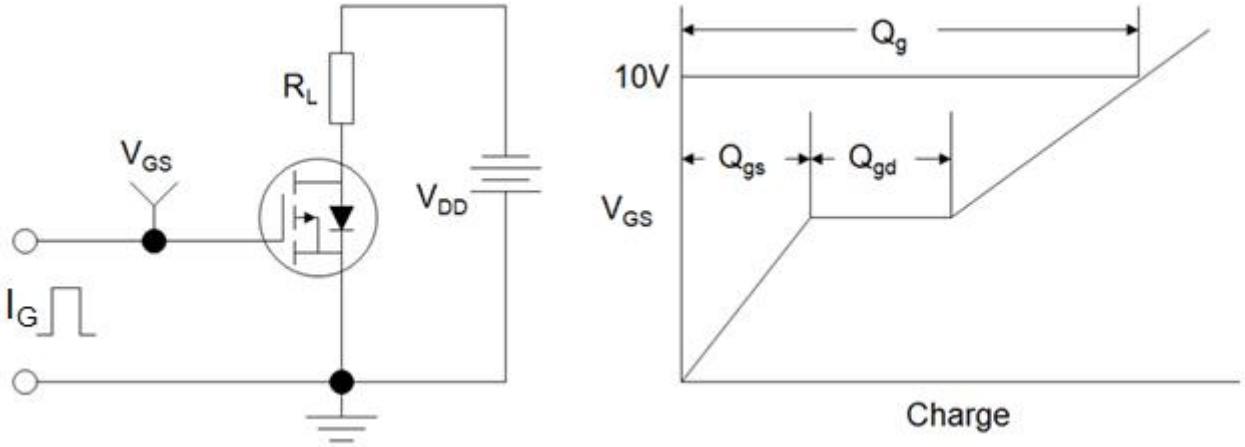
Specifications T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -100V, V_{GS} = 0V	--	--	-1	μA
Gate-Source Leakage	I_{GSS}	V_{GS} = ±20V	--	--	±10	uA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1.2	-1.6	-2.8	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -10V, I_D = -4A	--	180	200	mΩ
		V_{GS} = -4.5V, I_D = -3A	--	190	250	
Forward Transconductance	g_{FS}	V_{DS} = -5V,I_D = -4A	--	10	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -50V, f = 1.0MHz	--	1700	--	pF
Output Capacitance	C_{oss}		--	50	--	
Reverse Transfer Capacitance	C_{rss}		--	45	--	
Total Gate Charge	Q_g	V_{DD} = -50V, I_D = -4A, V_{GS} = -10V	--	32	--	nC
Gate-Source Charge	Q_{gs}		--	5	--	
Gate-Drain Charge	Q_{gd}		--	7	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = -50V, I_D = -4A, R_G = 9Ω	--	52	--	ns
Turn-on Rise Time	t_r		--	12	--	
Turn-off Delay Time	$t_{d(off)}$		--	38	--	
Turn-off Fall Time	t_f		--	28	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	-4	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = -4A, V_{GS} = 0V	--	--	-1.2	V
Reverse Recovery Charge	Q_{rr}	I_F = -4A, V_{GS} = 0V di/dt=-100A/us	--	35	--	nC
Reverse Recovery Time	T_{rr}		--	46	--	ns

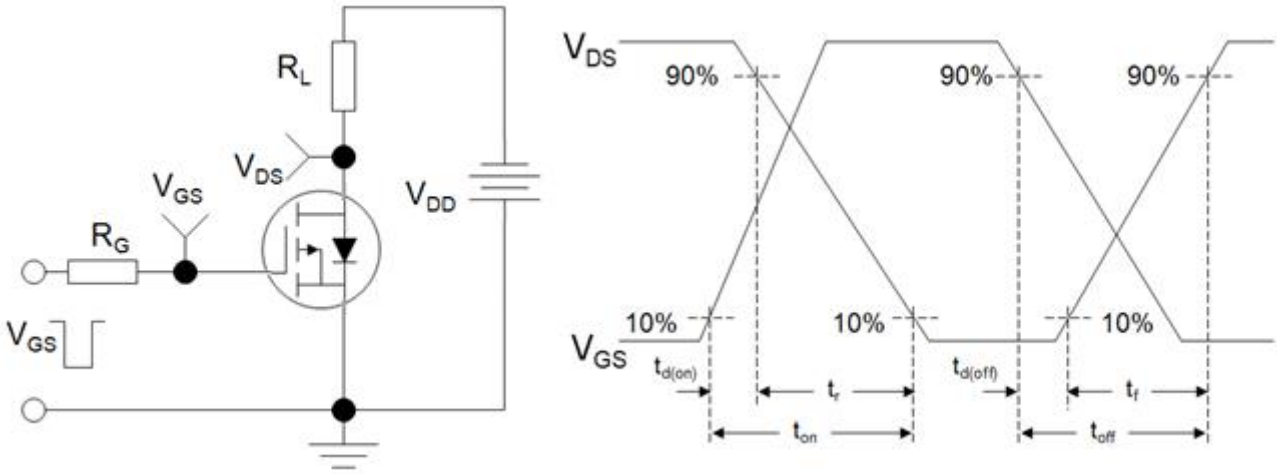
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G

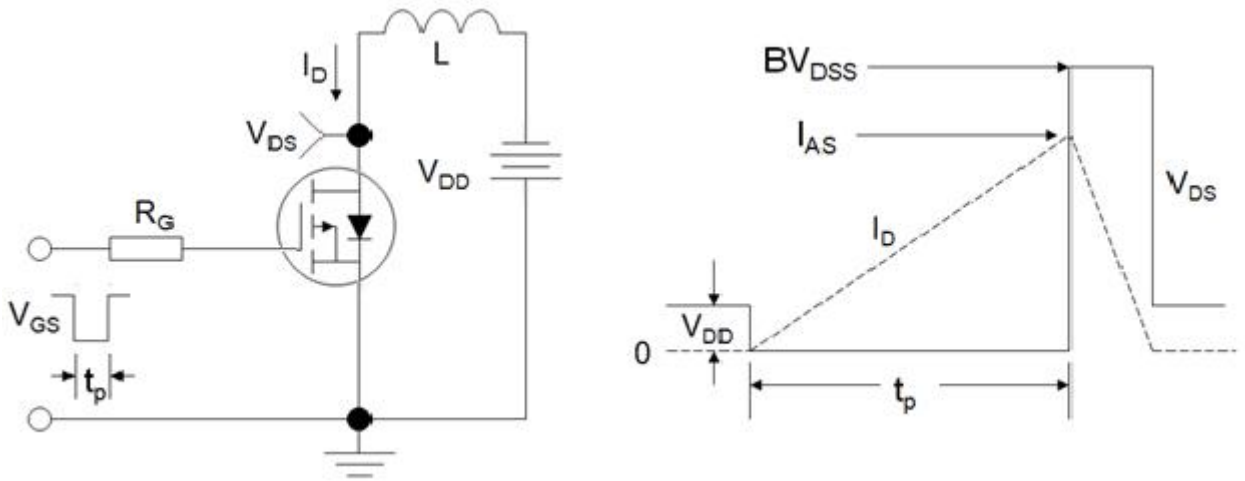
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

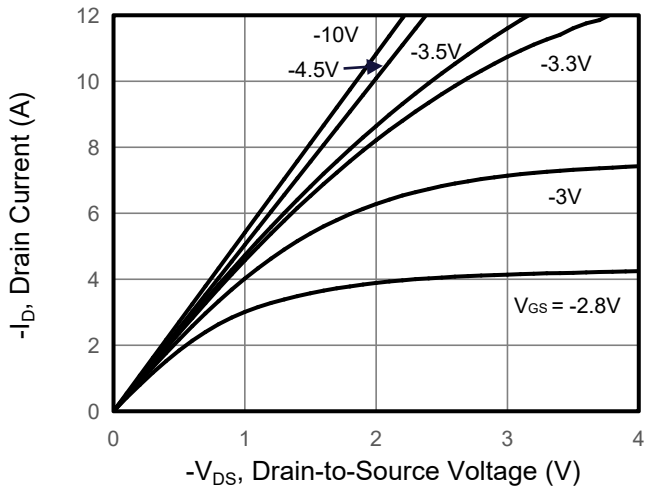


Figure 2. Transfer Characteristics

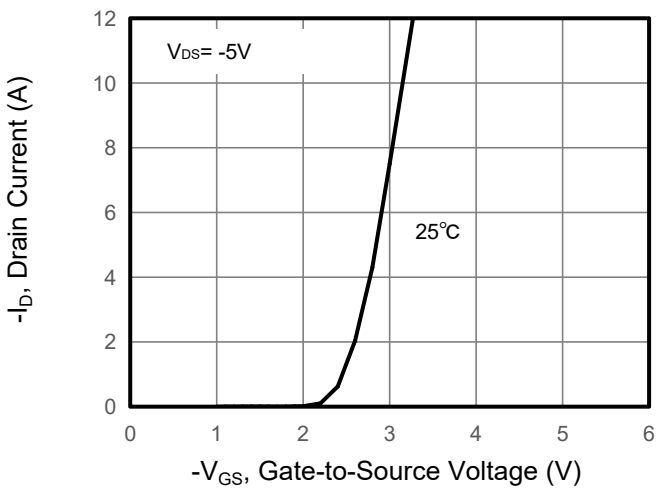


Figure 3.Drain Source On Resistance

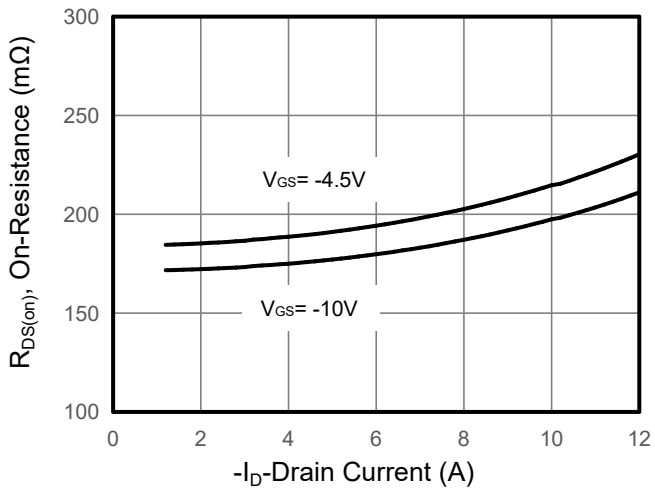


Figure 4. Gate Charge

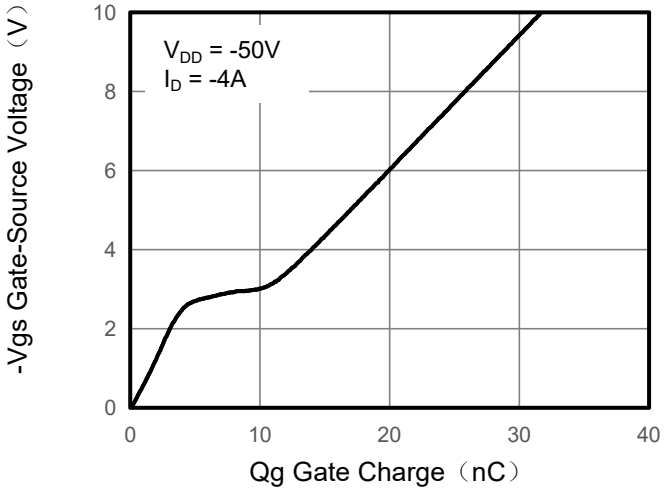


Figure 5. Capacitance

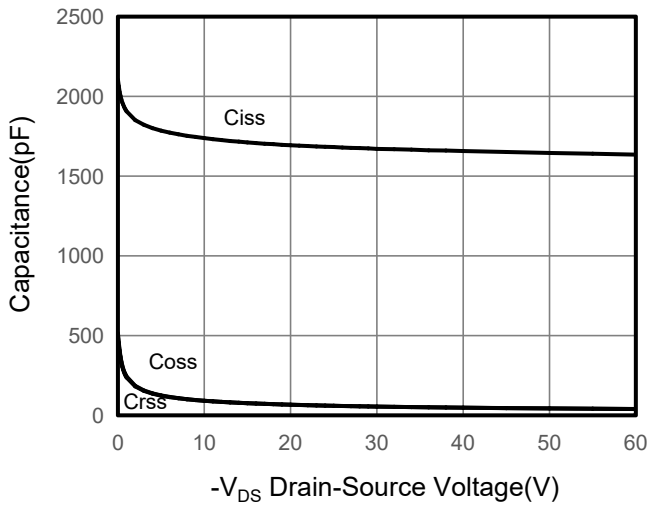
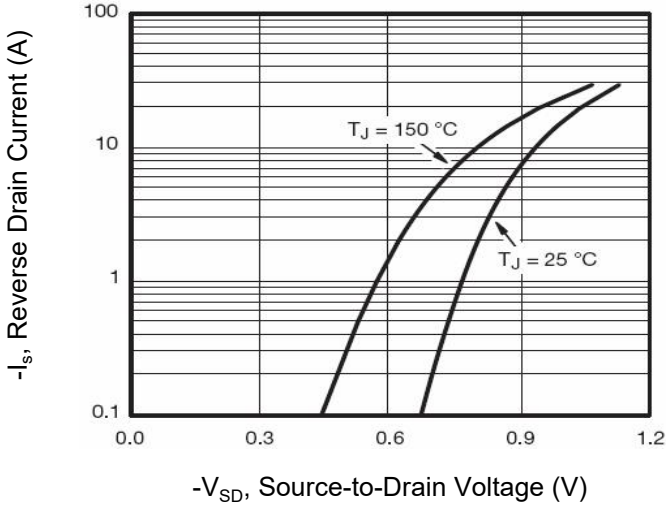


Figure 6. Source-Drain Diode Forward



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 7. Drain-Source On-Resistance

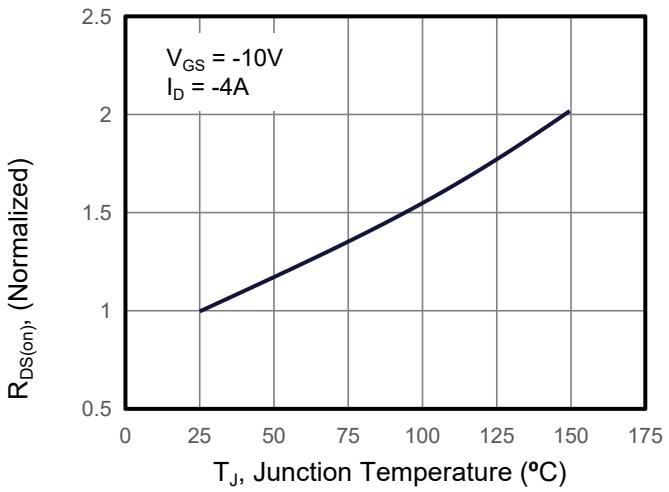


Figure 8. Safe Operation Area

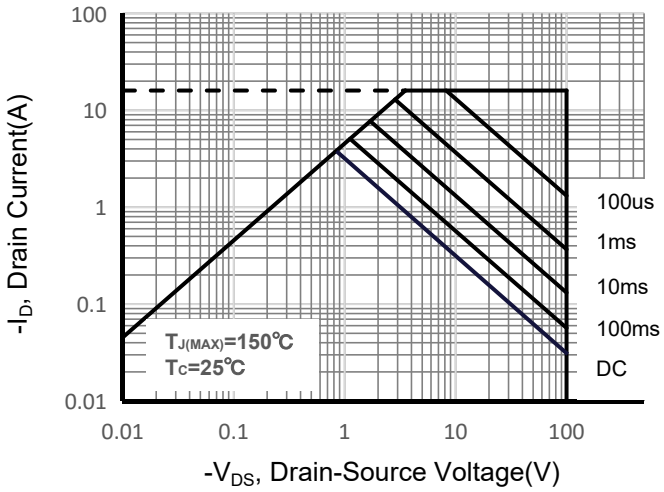


Figure 9. Maximum Continuous Drain Current vs Case Temperature

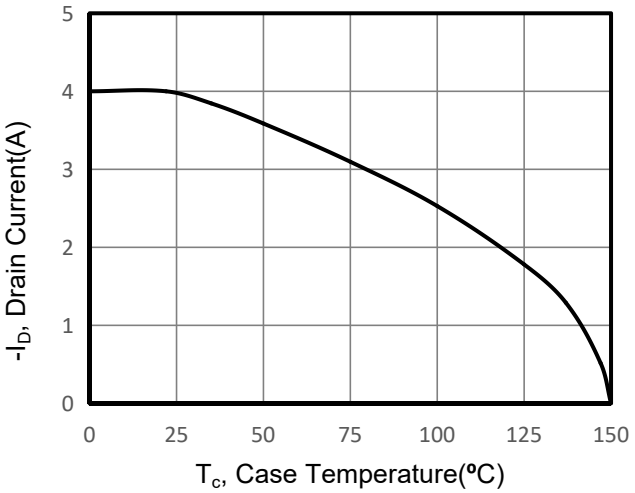
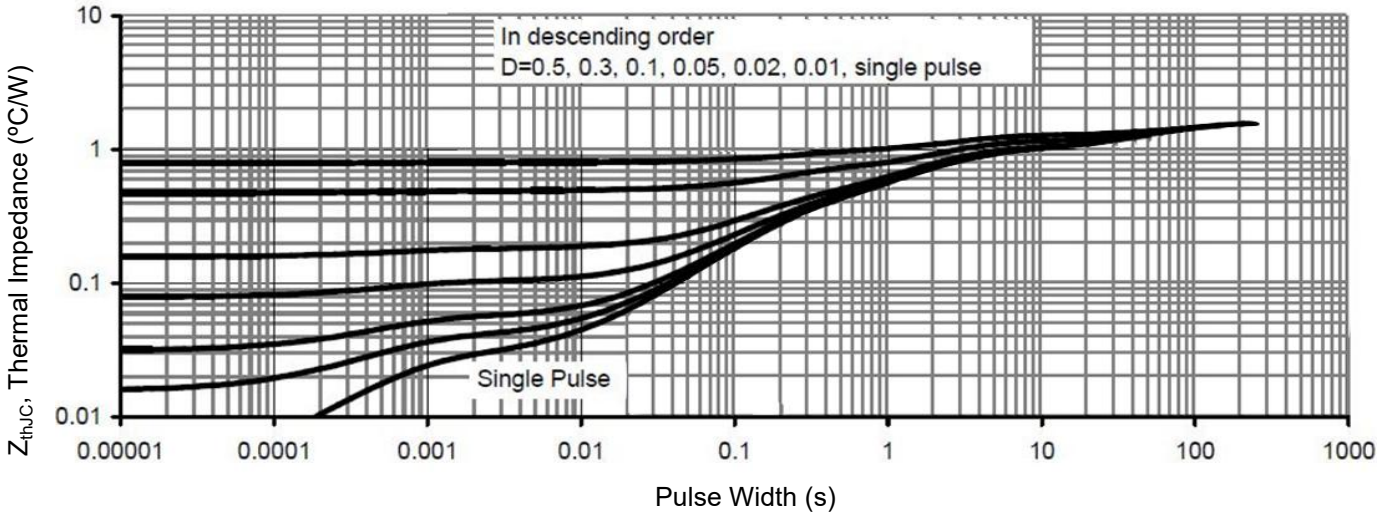
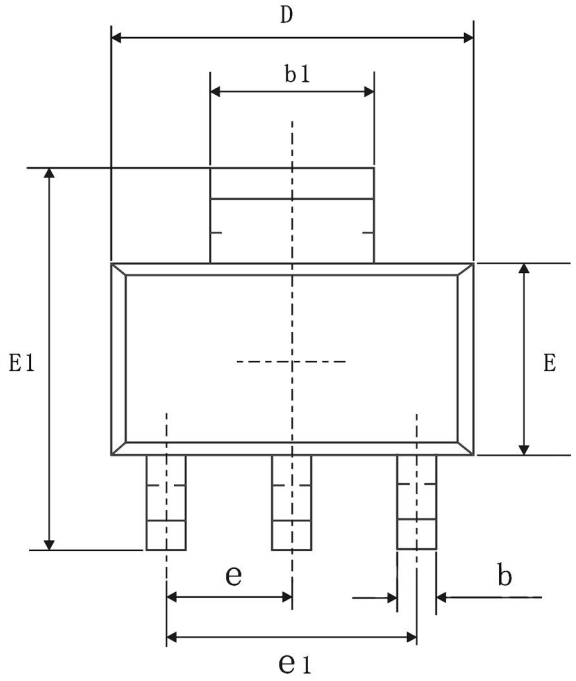


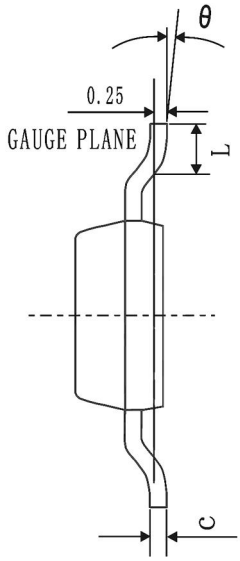
Figure 10. Normalized Maximum Transient Thermal Impedance



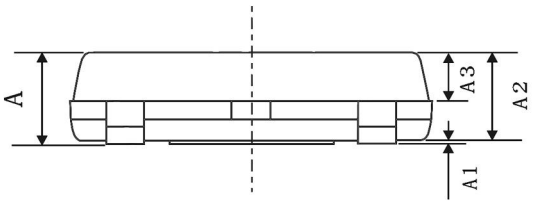
SOT-223 Package Mechanical Data



TOP VIEW



SIDE VIEW



SIDE VIEW

COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	——	——	1.80
A1	0.00	0.05	0.10
A2	1.50	1.60	1.70
A3	0.85	0.90	0.95
b	0.66	0.70	0.80
b1	2.96	3.00	3.10
c	0.25	0.30	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
E1	6.80	7.00	7.20
e1	4.40	4.60	4.80
L	0.90	——	1.15
θ	0°	5°	10°
e	2.3 BSC		